

**General Description**

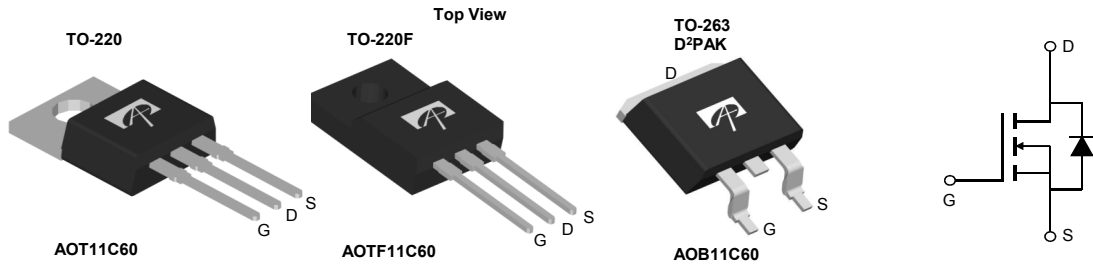
The AOT11C60 & AOB11C60 & AOTF11C60 are fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low  $R_{DS(ON)}$ ,  $C_{ISS}$  and  $C_{RSS}$  along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

For Halogen Free add "L" suffix to part number:  
 AOT11C60L & AOB11C60L & AOTF11C60L

**Product Summary**

$V_{DS} @ T_{J,max}$	700
$I_{DM}$	80A
$R_{DS(ON),max}$	< 0.44 $\Omega$
$Q_{g,typ}$	30nC
$E_{OSS} @ 400V$	5.1 $\mu$ J

100% UIS Tested  
 100%  $R_g$  Tested


**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	AOT11C60/AOB11C60	AOTF11C60	Units
Drain-Source Voltage	$V_{DS}$	600		V
Gate-Source Voltage	$V_{GS}$	$\pm 30$		V
Continuous Drain Current	$I_D$	$T_C=25^\circ\text{C}$	11	11*
		$T_C=100^\circ\text{C}$	9	9*
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	80		A
Avalanche Current <sup>C,J</sup>	$I_{AR}$	11		A
Repetitive avalanche energy <sup>C,J</sup>	$E_{AR}$	60		mJ
Single pulsed avalanche energy <sup>G</sup>	$E_{AS}$	750		mJ
MOSFET dv/dt ruggedness	dv/dt	100		V/ns
Peak diode recovery dv/dt		20		
Power Dissipation <sup>B</sup>	$P_D$	$T_C=25^\circ\text{C}$	278	50
		Derate above 25 $^\circ\text{C}$	2.2	0.4
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	$T_L$	300		$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	AOT11C60/AOB11C60	AOTF11C60	Units
Maximum Junction-to-Ambient <sup>A,D</sup>	$R_{\theta JA}$	65	65	$^\circ\text{C/W}$
Maximum Case-to-sink <sup>A</sup>	$R_{\theta CS}$	0.5	--	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.45	2.5	$^\circ\text{C/W}$

\* Drain current limited by maximum junction temperature.

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
<b>STATIC PARAMETERS</b>							
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	600			V	
		I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C		700			
BV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V		0.55		V/°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =600V, V <sub>GS</sub> =0V			1	μA	
		V <sub>DS</sub> =480V, T <sub>J</sub> =125°C			10		
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V			±100	nA	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =5V, I <sub>D</sub> =250μA	3	4	5	V	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =5.5A		0.36	0.44	Ω	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =40V, I <sub>D</sub> =5.5A		12		S	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.7	1	V	
I <sub>S</sub>	Maximum Body-Diode Continuous Current				11	A	
I <sub>SM</sub>	Maximum Body-Diode Pulsed Current <sup>C</sup>				80	A	
<b>DYNAMIC PARAMETERS</b>							
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =100V, f=1MHz		2000		pF	
C <sub>oss</sub>	Output Capacitance				84		pF
C <sub>o(er)</sub>	Effective output capacitance, energy related <sup>H</sup>	V <sub>GS</sub> =0V, V <sub>DS</sub> =0 to 480V, f=1MHz		60		pF	
C <sub>o(tr)</sub>	Effective output capacitance, time related <sup>I</sup>				107		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =100V, f=1MHz		2.8		pF	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		3.5		Ω	
<b>SWITCHING PARAMETERS</b>							
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =480V, I <sub>D</sub> =11A		30	42	nC	
Q <sub>gs</sub>	Gate Source Charge				14		nC
Q <sub>gd</sub>	Gate Drain Charge				4		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =300V, I <sub>D</sub> =11A, R <sub>G</sub> =25Ω		50		ns	
t <sub>r</sub>	Turn-On Rise Time				50		ns
t <sub>D(off)</sub>	Turn-Off DelayTime				70		ns
t <sub>f</sub>	Turn-Off Fall Time				32		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =11A, dI/dt=100A/μs, V <sub>DS</sub> =100V		485		ns	
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =11A, dI/dt=100A/μs, V <sub>DS</sub> =100V		7.2		μC	

A. The value of R<sub>θJA</sub> is measured with the device in a still air environment with T<sub>A</sub>=25° C.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150° C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25° C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150° C. The SOA curve provides a single pulse rating.

G. L=60mH, I<sub>AS</sub>=5A, V<sub>DD</sub>=150V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25° C.

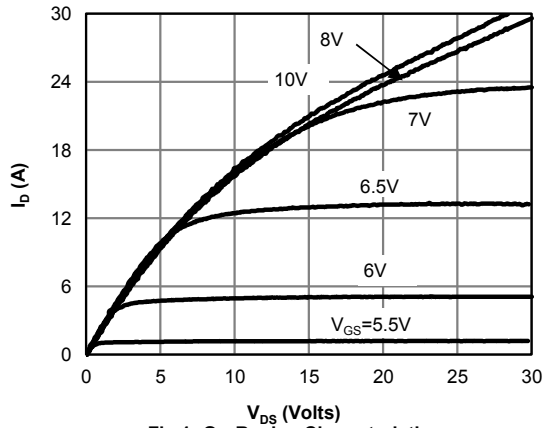
H. C<sub>o(er)</sub> is a fixed capacitance that gives the same stored energy as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>(BR)DSS</sub>.

I. C<sub>o(tr)</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>(BR)DSS</sub>.

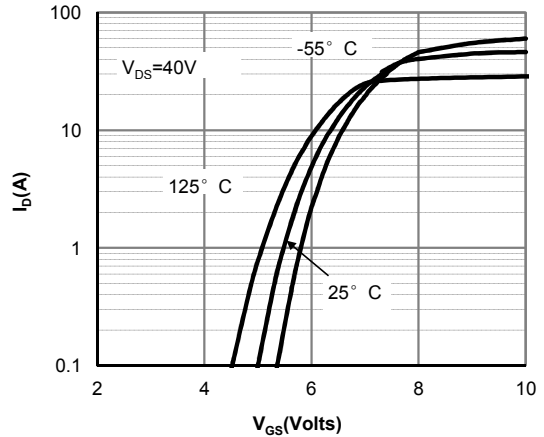
J. L=1.0mH, V<sub>DD</sub>=150V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25° C.

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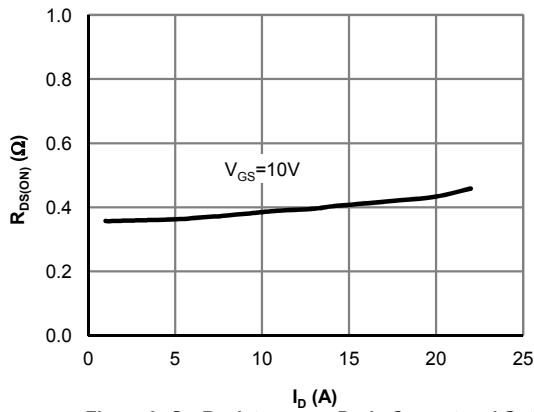
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



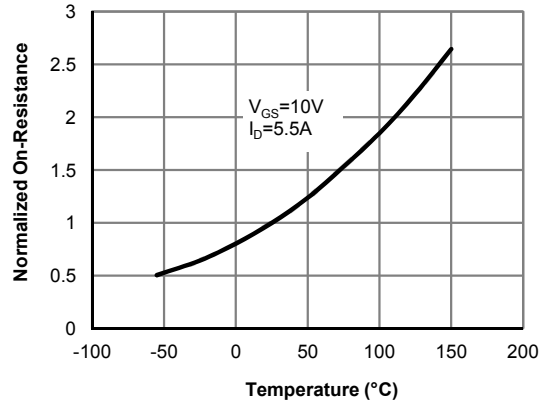
**Fig 1: On-Region Characteristics**



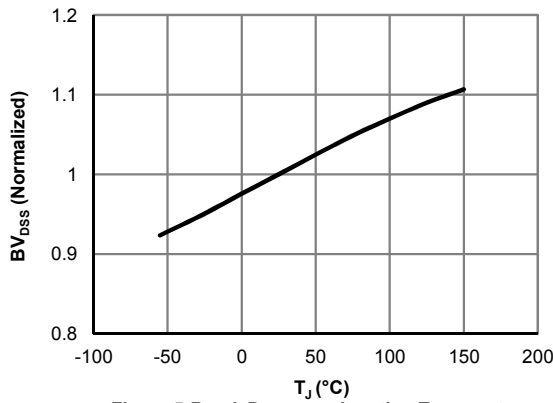
**Figure 2: Transfer Characteristics**



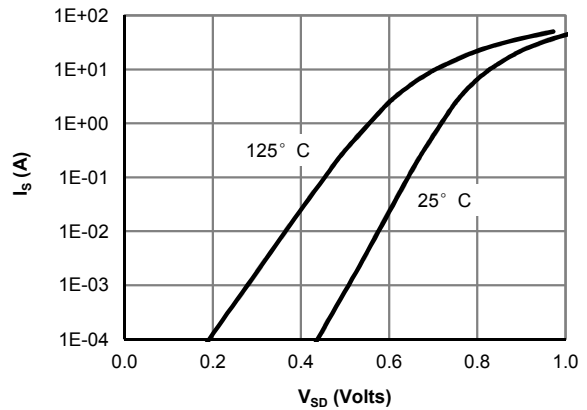
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**

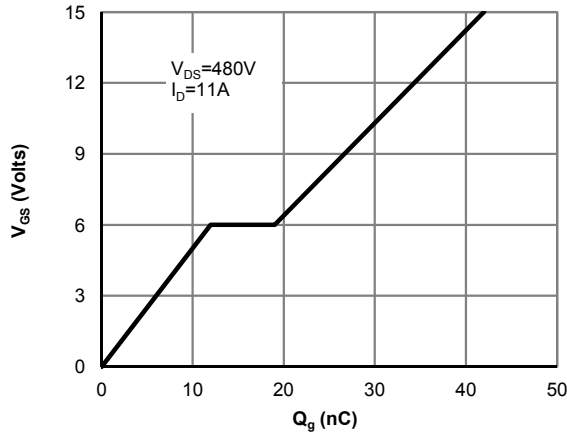


**Figure 5: Break Down vs. Junction Temperature**

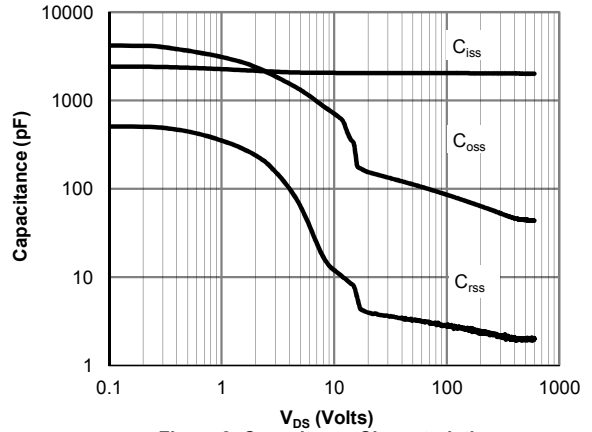


**Figure 6: Body-Diode Characteristics (Note E)**

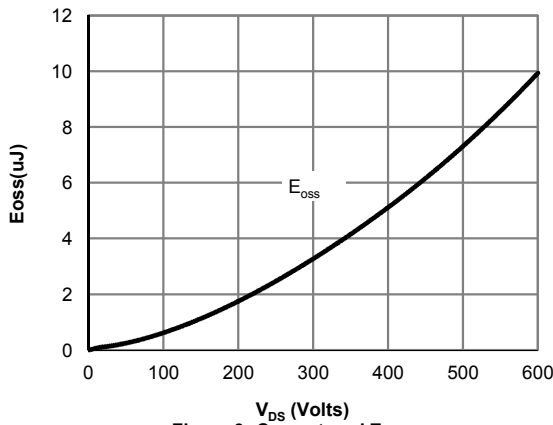
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



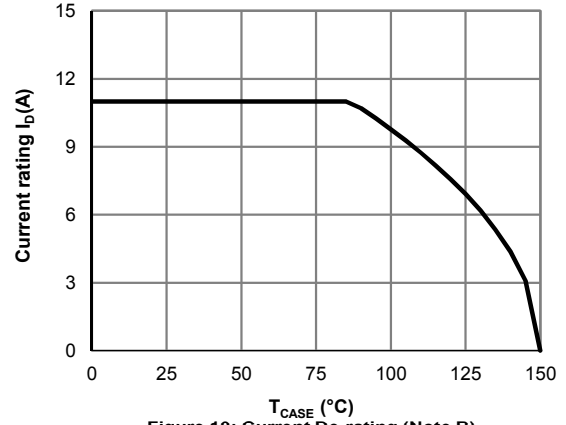
**Figure 7: Gate-Charge Characteristics**



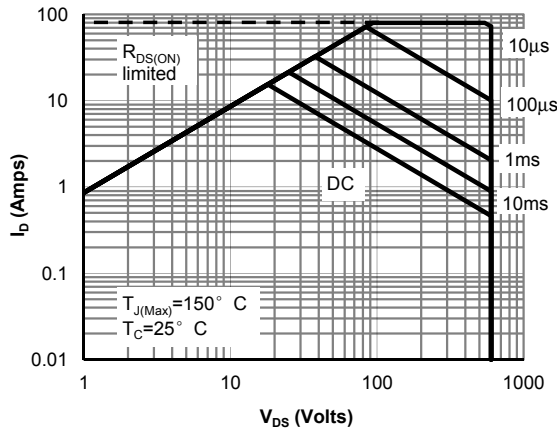
**Figure 8: Capacitance Characteristics**



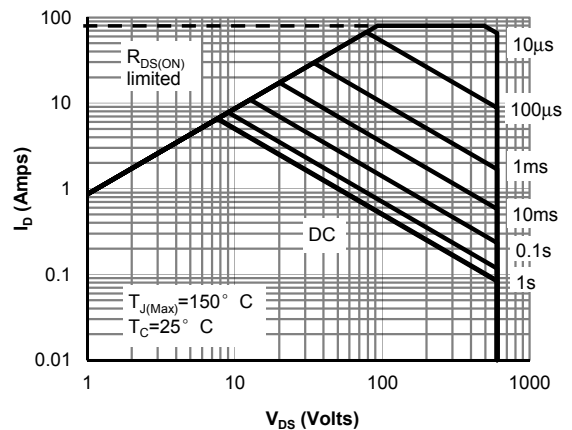
**Figure 9: Coss stored Energy**



**Figure 10: Current De-rating (Note B)**

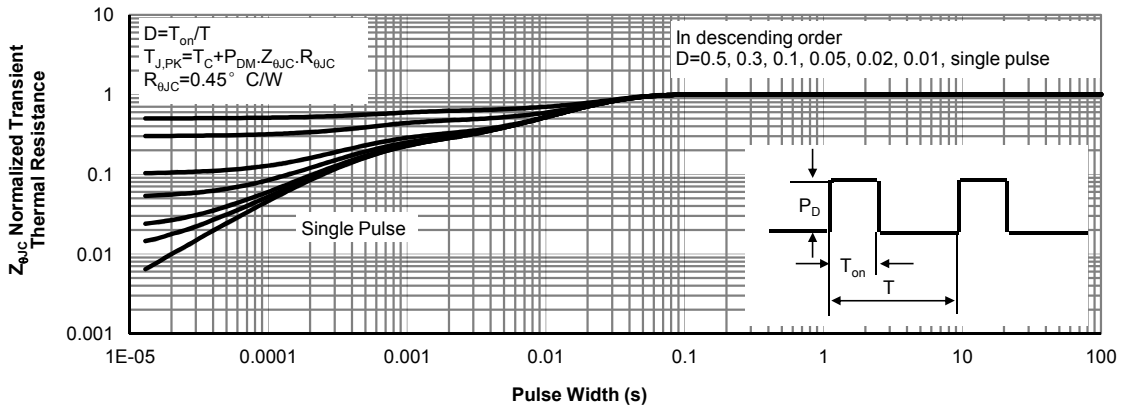


**Figure 11: Maximum Forward Biased Safe Operating Area for AOT(B)11C60 (Note F)**

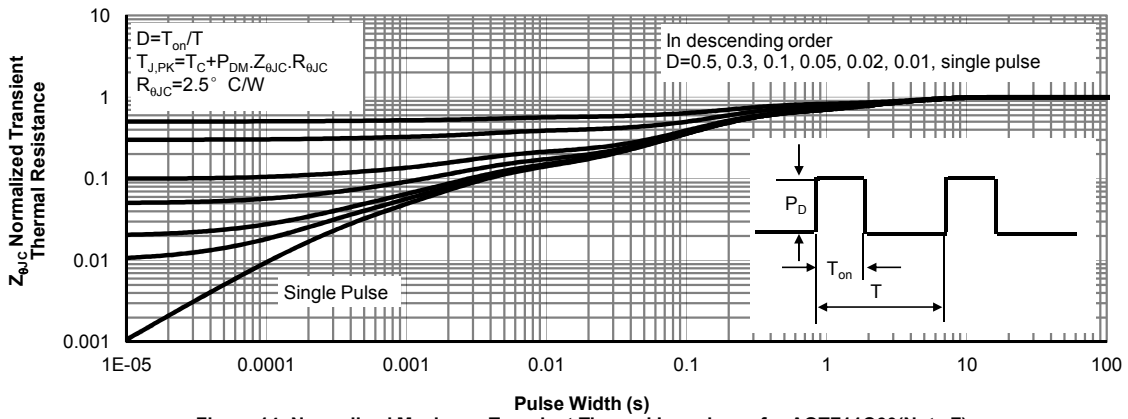


**Figure 12: Maximum Forward Biased Safe Operating Area for AOTF11C60 (Note F)**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

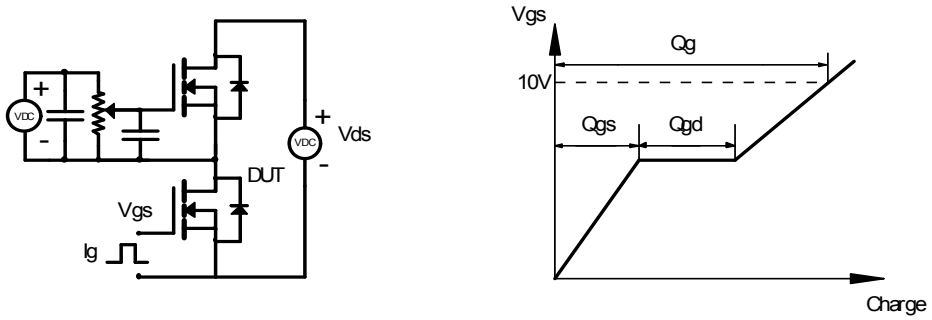


**Figure 13: Normalized Maximum Transient Thermal Impedance for AOT(B)11C60 (Note F)**

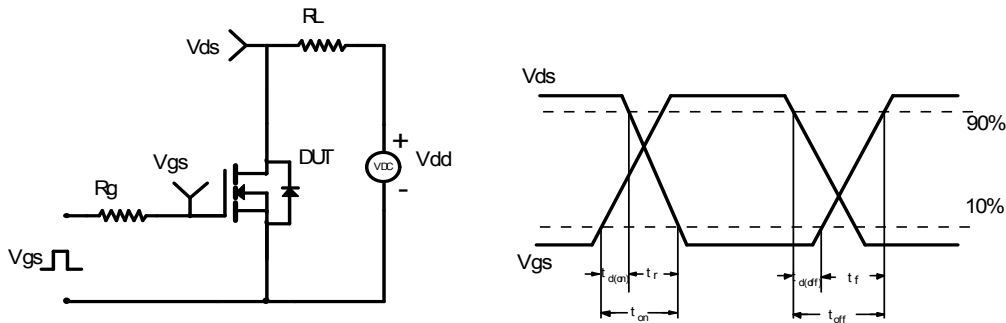


**Figure 14: Normalized Maximum Transient Thermal Impedance for AOTF11C60 (Note F)**

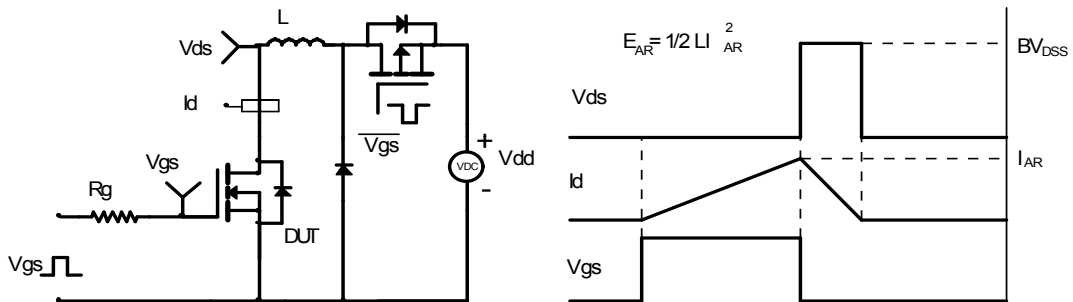
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

